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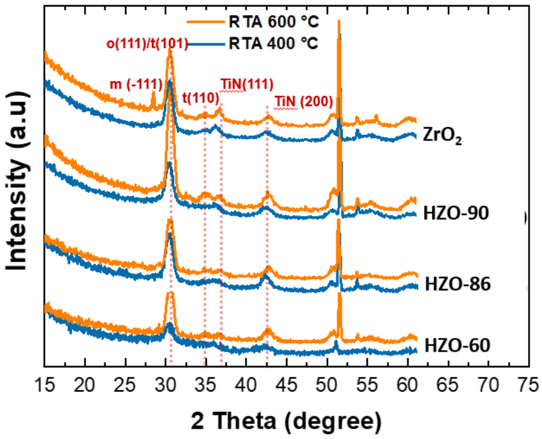

Fig. 1. XRD patterns of 8 nm HZO thin films with varying ZrO_2 content under different annealing temperatures (400 °C and 600 °C).

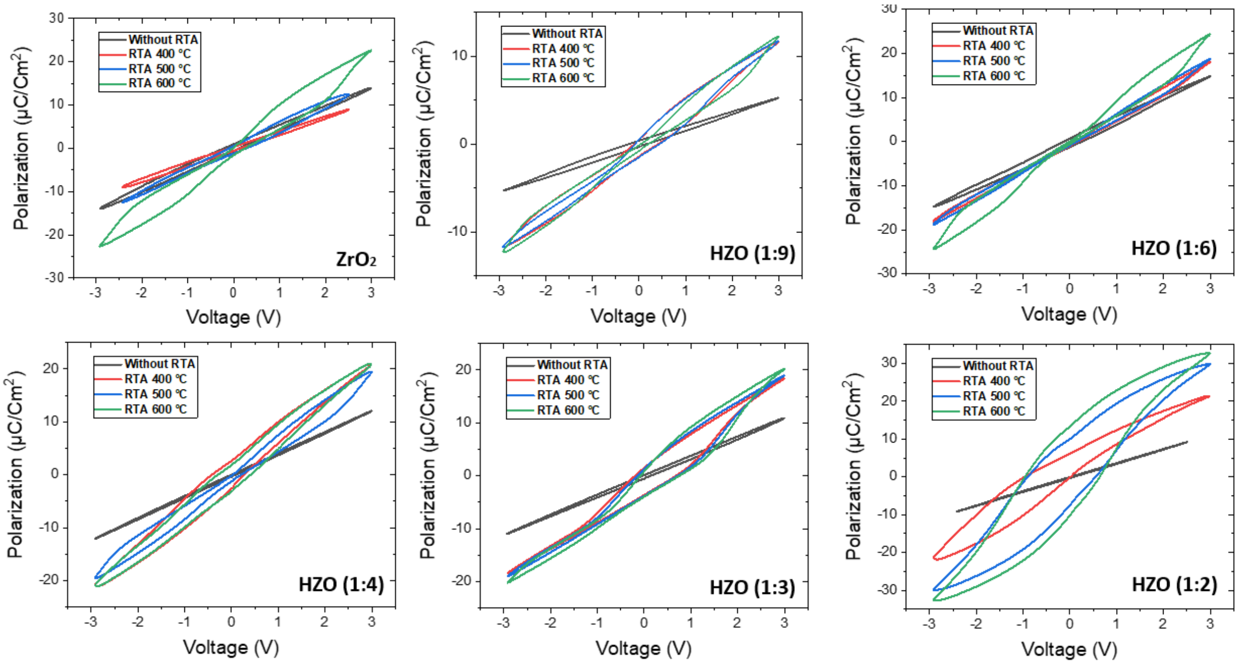

Fig. 2. Polarization–electric field hysteresis response of HZO films (8 nm) as-deposited and after rapid thermal annealing at different temperatures.